SILICON MULTIPLIER VARACTOR DIODE

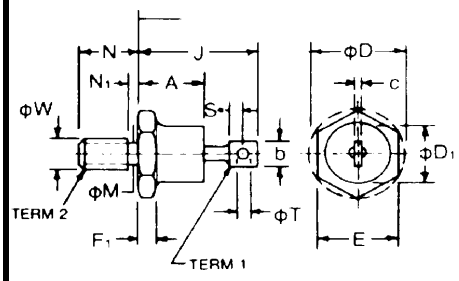
DESCRIPTION:

The **1N4387** is a High Power Silicon Multiplier Varactor Diode.

MAXIMUM RATINGS

I_O	200 mA
V_R	150 V
P_{DISS}	20 W @ T_C = 25 ^{O}C
T_J	-65 ^{O}C to +150 ^{O}C
T_{STG}	-65 ^{O}C to +175 ^{O}C
θ_{JC}	5.0 ^{O}C/W

PACKAGE STYLE DO- 4



1 = Anode
2 = Cathode

SYMBOL	DIMENSIONS			
	INCHES		MILLIMETERS	
	MIN.	MAX.	MIN.	MAX.
A		0.405		10.28
b		0.250		6.35
c				
ΦD		0.505		12.82
ΦD1	0.265	0.424	6.74	10.76
E	0.423	0.438	10.75	11.12
F1	0.075	0.175	1.91	4.44
J	0.600	0.800	15.24	20.32
ΦM	0.163	0.189	4.15	4.80
N	0.422	0.453	10.72	11.50
N1		0.078		1.98
S				
ΦT	0.060	0.095	1.53	2.41
ΦW	10-32	UNF-2A	10-32	UNF-2A

CHARACTERISTICS T_C = 25 ^{O}C

SYMBOL	TEST CONDITIONS		MINIMUM	TYPICAL	MAXIMUM	UNITS
V_{BR}	I_R = 10 μA		150			V
C_T	V_R = 6.0 V	f = 1.0 MHz			35	pF
Q	V_R = 6.0 V	f = 50 MHz		200		---
f_{in}					150	MHz
$P_{OUT(x3)}$	P_{IN} = 30 W	F_{IN} = 150 MHz	15		30	W

Specifications are subject to change without notice.